PRODUCT LINEUP

■ Symmetrical Block SmartVoltage Flash Memories

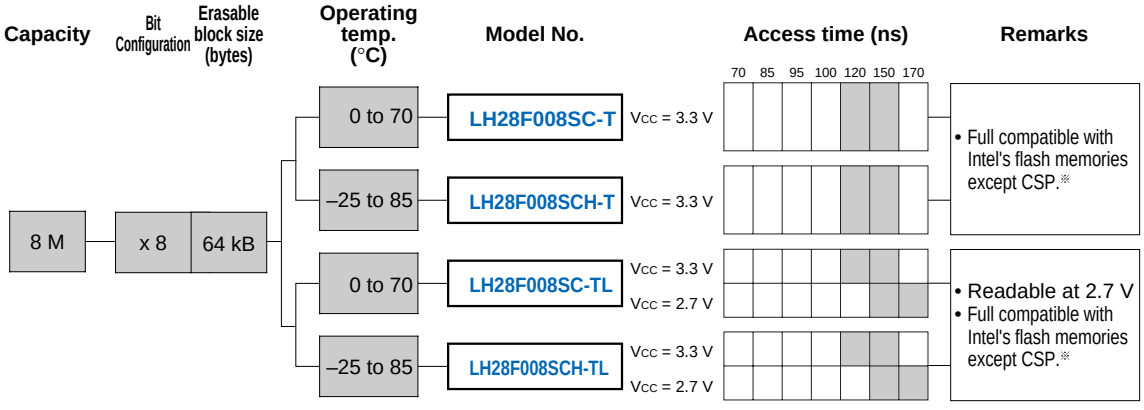
Supply voltage	Smart voltage	Supply voltage can be selected automatically from following combinations; V_{CC} = 3.3 V, V_{PP} = 3.3 V/V_{CC} = 3.3 V, V_{PP} = 5 V/V_{CC} = 3.3 V, V_{PP} = 12 V/ V_{CC} = 5 V, V_{PP} = 5 V/V_{CC} = 5 V, V_{PP} = 12 V

Capacity	Bit Configuration	Erasable block size (bytes/words)	Operating temp. (°C)	Model No.	Access time (ns) (70 / 85 / 95 / 100 / 120 / 150 / 170)	Remarks
2 M	x 8	64 kB	0 to 70	LH28F002SC-L	V_{CC} = 5 V V_{CC} = 3.3 V V_{CC} = 2.7 V	• Readable at 2.7 V
			–40 to 85	LH28F002SCH-L	V_{CC} = 5 V V_{CC} = 3.3 V V_{CC} = 2.7 V	
4 M	x 8	64 kB	0 to 70	LH28F004SC-L	V_{CC} = 5 V V_{CC} = 3.3 V V_{CC} = 2.7 V	• Readable at 2.7 V • Full compatible with Intel's flash memories except CSP.※
			–40 to 85	LH28F004SCH-L	V_{CC} = 5 V V_{CC} = 3.3 V V_{CC} = 2.7 V	
8 M	x 8	64 kB	0 to 70	LH28F008SC	V_{CC} = 5 V V_{CC} = 3.3 V	• Full compatible with Intel's flash memories except CSP.※
			–25 to 85	LH28F008SCH	V_{CC} = 5 V V_{CC} = 3.3 V	
			0 to 70	LH28F008SC-L	V_{CC} = 5 V V_{CC} = 3.3 V V_{CC} = 2.7 V	• Readable at 2.7 V • Full compatible with Intel's flash memories except CSP.※
			–25 to 85	LH28F008SCH-L	V_{CC} = 5 V V_{CC} = 3.3 V V_{CC} = 2.7 V	
	x 16	32 kW	0 to 70	LH28F800SG-L (FOR TSOP, CSP)	V_{CC} = 5 V V_{CC} = 3.3 V V_{CC} = 2.7 V	• Readable, programmable and erasable at 2.7 V
				LH28F800SG-L (FOR SOP)	V_{CC} = 5 V V_{CC} = 3.3 V V_{CC} = 2.7 V	
			–40 to 85	LH28F800SGH-L (FOR TSOP, CSP)	V_{CC} = 5 V V_{CC} = 3.3 V V_{CC} = 2.7 V	
16 M	x 8	64 kB	0 to 70	LH28F016SC-L	V_{CC} = 5 V V_{CC} = 3.3 V V_{CC} = 2.7 V	• Readable at 2.7 V • Full compatible with Intel's flash memories except CSP.※
			–40 to 85	LH28F016SCH-L	V_{CC} = 5 V V_{CC} = 3.3 V V_{CC} = 2.7 V	

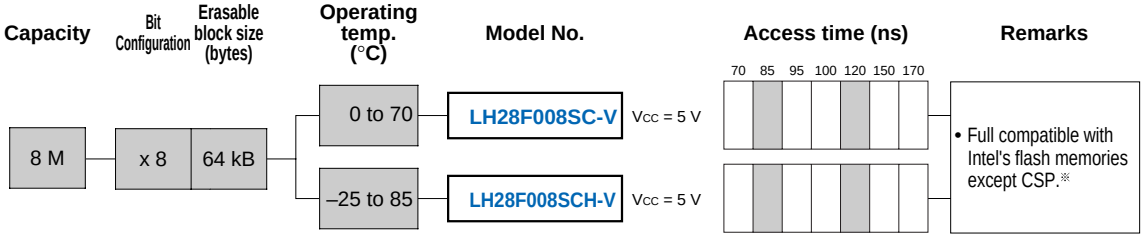
※ Make sure of the actual pin spec. etc. in the latest specifications.

■ Symmetrical Block SmartVoltage Flash Memories (contd.)

Supply voltage	Smart 3	Supply voltage can be selected automatically from following combinations; V_{CC} = 3.3 V, V_{PP} = 3.3 V/V_{CC} = 3.3 V, V_{PP} = 12 V



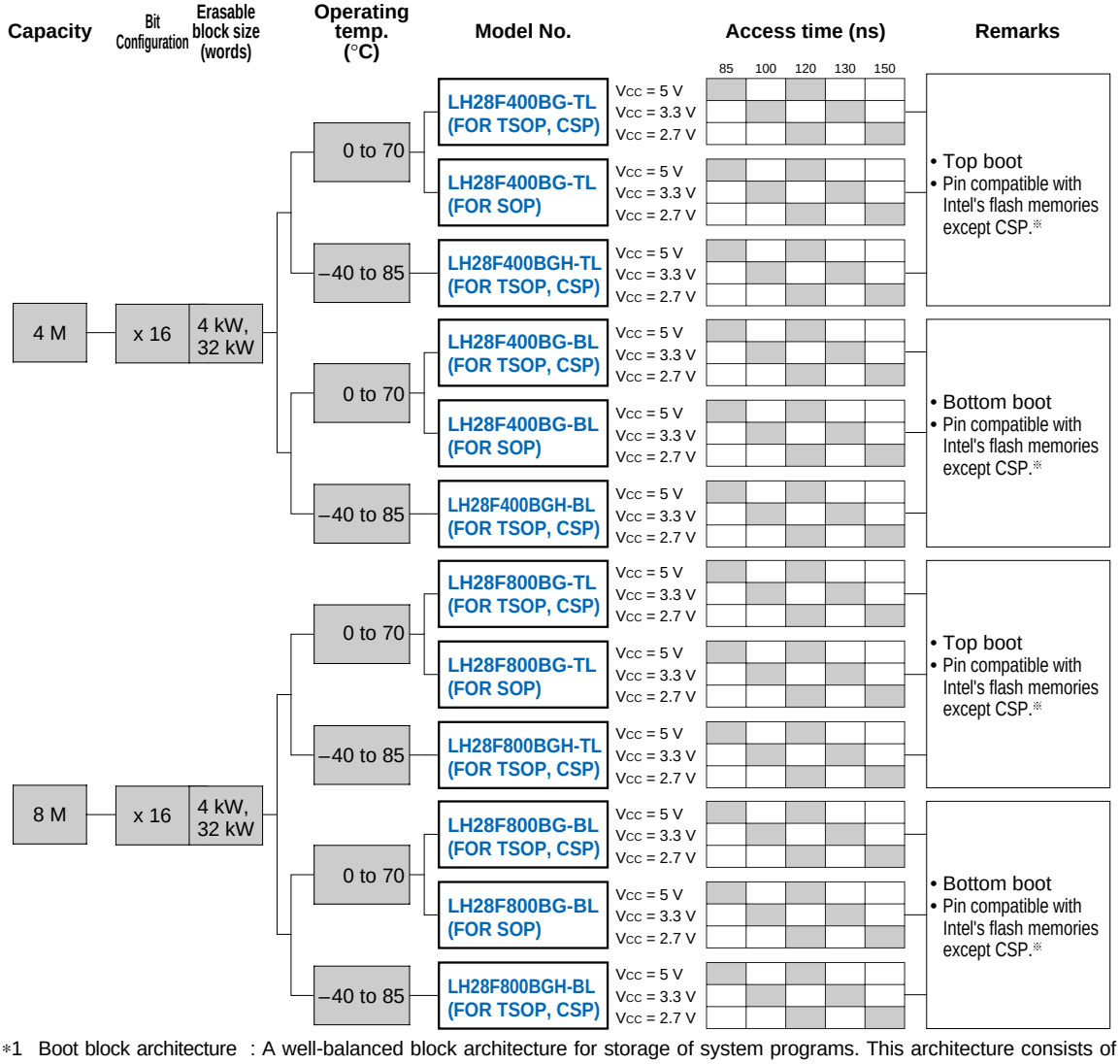
Supply voltage	Smart 5	Supply voltage can be selected automatically from following combinations; V_{CC} = 5 V, V_{PP} = 5 V/V_{CC} = 5 V, V_{PP} = 12 V



※ Make sure of the actual pin spec. etc. in the latest specifications.

■ Boot Block SmartVoltage Flash Memories *1

Supply voltage	Smart Voltage	Supply voltage can be selected automatically from following combinations; V_{CC} = 3.3 V, V_{PP} = 3.3 V/V_{CC} = 3.3 V, V_{PP} = 5 V/V_{CC} =3.3 V, V_{PP} = 12 V/ V_{CC} = 5 V, V_{PP} = 5 V/V_{CC} = 5 V, V_{PP} = 12 V (Operable at V_{CC} = 2.7 V, V_{PP} = 2.7 V)



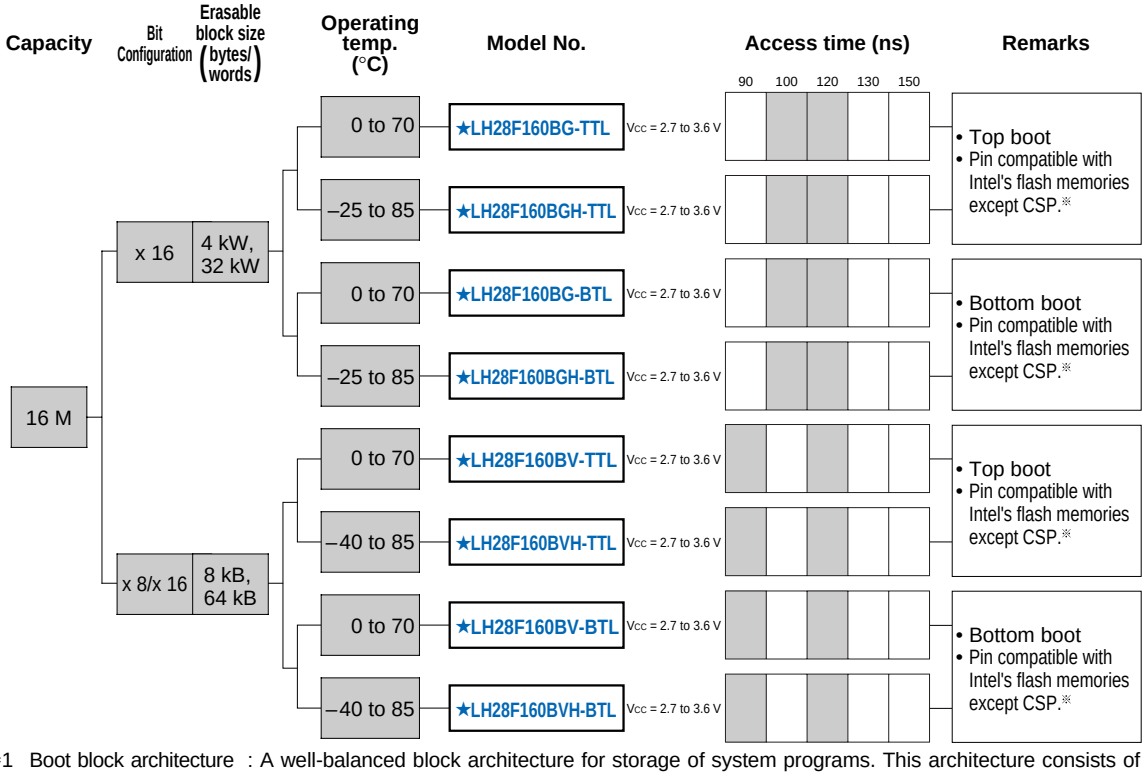
*1 Boot block architecture : A well-balanced block architecture for storage of system programs. This architecture consists of small-sized blocks (4 k-word) for storage of boot code and parameters, and larger size symmetrical blocks (32 k-word) for storage of main code.

※ Make sure of the actual pin spec. etc. in the latest specifications.

■ Boot Block Flash Memories (contd.) *1

★ Under development

Supply voltage	Smart 3	Supply voltage can be selected automatically from following combinations; V_{CC} = 2.7 to 3.6 V, V_{PP} = 2.7 to 3.6 V/V_{CC} = 2.7 to 3.6 V, V_{PP} = 12 V



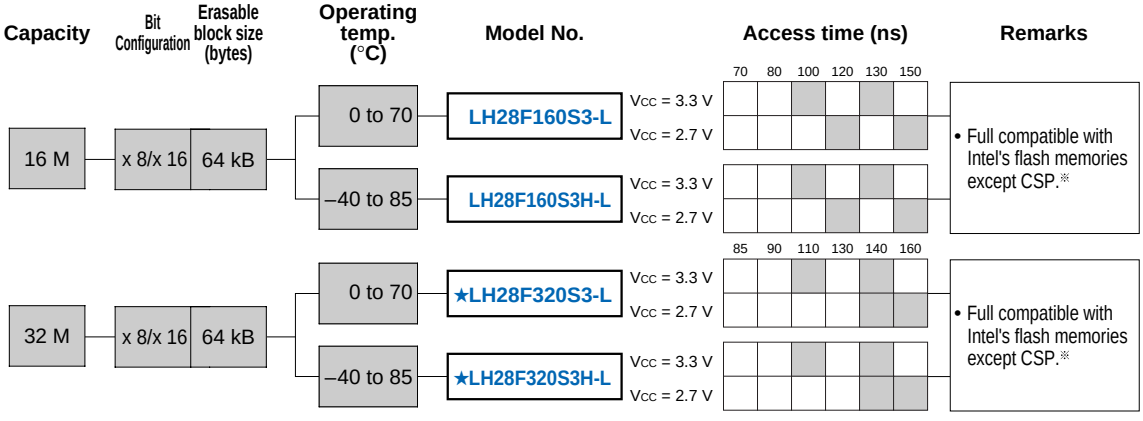
*1 Boot block architecture : A well-balanced block architecture for storage of system programs. This architecture consists of small-sized blocks (4 k-word) for storage of boot code and parameters, and larger size symmetrical blocks (32 k-word) for storage of main code.

※ Make sure of the actual pin spec. etc. in the latest specifications.

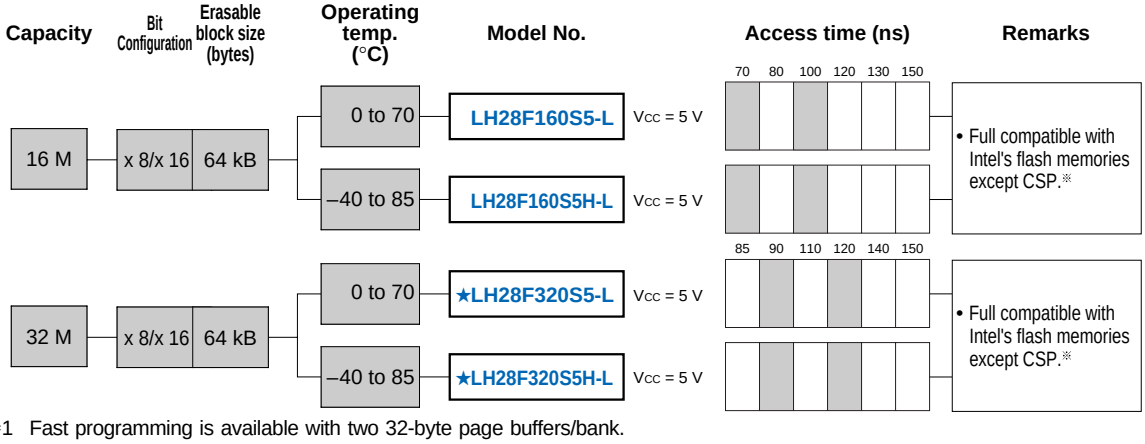
■ Fast Programming Flash Memories *1

★ Under development

Supply voltage	Smart 3	Supply voltage can be selected automatically from following combinations; V_{CC} = 3.3 V, V_{PP} = 3.3 V/V_{CC} = 3.3 V, V_{PP} = 5 V (Operable at V_{CC} = 2.7 V, V_{PP} = 2.7 V)



Supply voltage	Smart 5	V_{CC} = 5 V, V_{PP} = 5 V



*1 Fast programming is available with two 32-byte page buffers/bank.

※ Make sure of the actual pin spec. etc. in the latest specifications.

■ Dual Work Flash Memories ∗1

Supply voltage	V_{CC} = 2.9 to 3.3 V, V_{PP} = 2.9 to 3.3 V

Capacity	Bit Configuration	Erasable block size (bytes)	Operating temp. (°C)	Model No.		Access time (ns) 85 90 100 120 130 150	Remarks
8 M	x 8	64 kB	–40 to 85	LH28F008SCHSD-ZL	V_{CC} = 2.7 to 3.3 V		• Readable at 2.7 V

Supply voltage	Smart Voltage	Supply voltage can be selected automatically from following combinations; V_{CC} = 3.3 V, V_{PP} = 3.3 V/V_{CC} = 3.3 V, V_{PP} = 5 V/V_{CC} = 3.3 V, V_{PP} = 12 V/ V_{CC} = 5 V, V_{PP} = 5 V/V_{CC} = 5 V, V_{PP} = 12 V (Operable at V_{CC} = 2.7 V, V_{PP} = 2.7 V)

Capacity	Bit Configuration	Erasable block size (words)	Operating temp. (°C)	Model No.		Access time (ns) 85 90 100 120 130 150	Remarks
16 M	x 16	32 kW	–10 to 70	LH28F160SGED-L10	V_{CC} = 5 V V_{CC} = 3.3 V V_{CC} = 2.7 V		—

Supply voltage	Smart 3	Supply voltage can be selected automatically from following combinations; V_{CC} = 3.3 V, V_{PP} = 3.3 V/V_{CC} = 3.3 V, V_{PP} = 5 V (Operable at V_{CC} = 2.7 V, V_{PP} = 2.7 V)

Capacity	Bit Configuration	Erasable block size (bytes)	Operating temp. (°C)	Model No.		Access time (ns) 85 90 100 120 130 150	Remarks
32 M	x 8/x 16	64 kB	0 to 70	LH28F320S3TD-L10	V_{CC} = 3.3 V V_{CC} = 2.7 V		—

■ Dual 5 V/12 V Power Supply Flash Memories ∗1

Supply voltage	V_{CC} = 5 V, V_{PP} = 12 V

Capacity	Bit Configuration	Erasable block size (bytes)	Operating temp. (°C)	Model No.		Access time (ns) 85 90 100 120 130 150	Remarks
8 M	x 8	64 kB	0 to 70	LH28F008SA-K	V_{CC} = 5 V		• Full compatible with Intel's flash memories except CSP.※
			–25 to 85	LH28F008SAH-K	V_{CC} = 5 V		

∗1 Capable of performing erase, write and read for each bank independently.
(Impossible to perform read from both banks at a time.)

※ Make sure of the actual pin spec. etc. in the latest specifications.